

Radiation	Type	Technology	Electrodes
Infrared	Point Source	AlGaAs/GaAs	N (cathode) up

	typ. dimensions (μm)
	<p>typ. thickness 260 (± 20) μm</p> <p><u>cathode</u> gold alloy, 1.5 μm</p> <p><u>anode</u> gold alloy, 0.5 μm</p>

Maximum Ratings

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			50	mA

Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.7	1.9	V
Reverse voltage	$I_R = 10 \mu\text{A}$	V_R	5			V
Radiant power*	$I_F = 20 \text{ mA}$	Φ_e	0.3	0.6		mW
Peak wavelength	$I_F = 20 \text{ mA}$	λ_P	730	740	750	nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		45		nm
Switching time	$I_F = 20 \text{ mA}$	t_r, t_f		50		ns

*Measured on bare chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	$\Phi_e(\text{typ})$ [mW]	$V_F(\text{typ})$ [V]	Quantity
ELC-740-27-70				

We reserve the right to make changes to improve technical design and may do so without further notice.
Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.

EPIGAP Optoelektronik GmbH, D-12555 Berlin, Köpenicker Str.325 b, Haus 201

Tel.: +49-30-6576 2543, Fax : +49-30-6576 2545